

MMBV432LT1

Preferred Device

Silicon Tuning Diode

This device is designed for FM tuning, general frequency control and tuning, or any top-of-the-line application requiring back-to-back diode configuration for minimum signal distortion and detuning. This device is supplied in the SOT-23 plastic package for high volume, pick and place assembly requirements.

Features

- High Figure of Merit – $Q = 150$ (Typ) @ $V_R = 2.0$ Vdc, $f = 100$ MHz
- Guaranteed Capacitance Range
- Dual Diodes – Save Space and Reduce Cost
- Surface Mount Package
- Available in 8 mm Tape and Reel
- Monolithic Chip Provides Improved Matching – Guaranteed $\pm 1.0\%$ (Max) Over Specified Tuning Range
- Pb-Free Package is Available

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	14	Vdc
Forward Current	I_F	200	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Junction Temperature	T_J	+125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

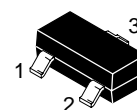
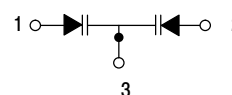
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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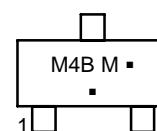
<http://onsemi.com>

DUAL VOLTAGE VARIABLE CAPACITANCE DIODE



SOT-23 (TO-236)
CASE 318
STYLE 9

MARKING DIAGRAM



M4B = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBV432LT1	SOT-23	3,000 / Tape & Reel
MMBV432LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBV432LT1

ELECTRICAL CHARACTERISTICS (EACH DIODE) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	14	–	–	Vdc
Reverse Voltage Leakage Current ($V_R = 9.0 \text{ Vdc}$)	I_R	–	–	100	nAdc
Diode Capacitance ($V_R = 2.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_T	43	–	48.1	pF
Capacitance Ratio C2/C8 ($f = 1.0 \text{ MHz}$)	C_R	1.5	–	2.0	–
Figure of Merit ($V_R = 2.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	Q	100	150	–	–

MMBV432LT1

TYPICAL CHARACTERISTICS (Each Diode)

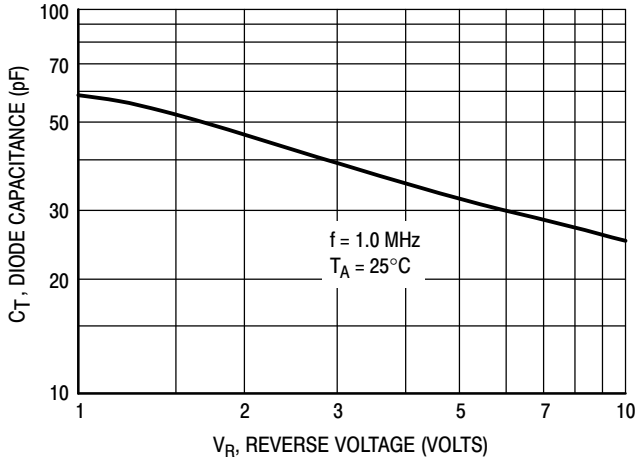


Figure 1. Diode Capacitance

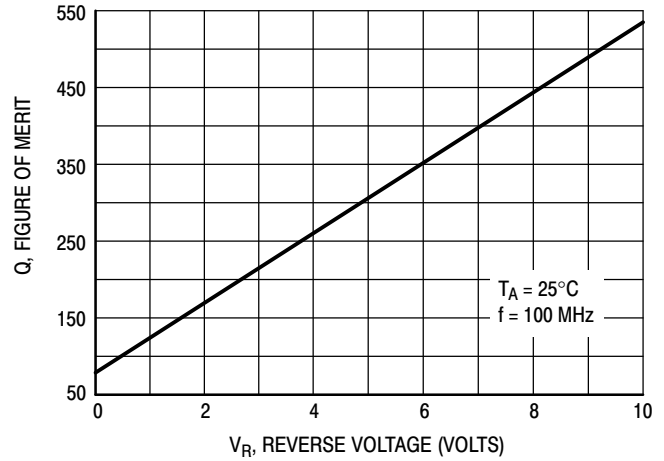


Figure 2. Figure of Merit versus Voltage

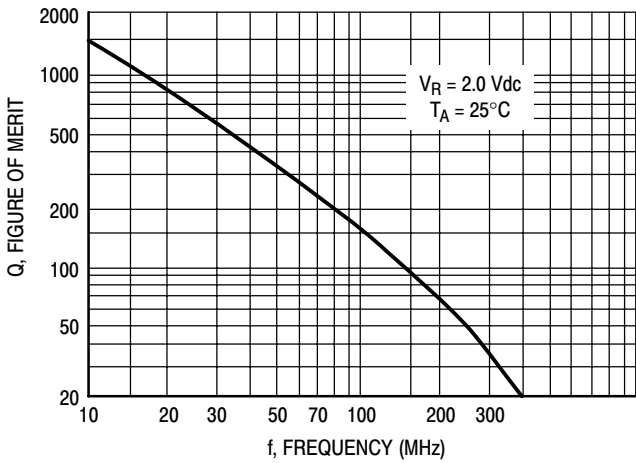


Figure 3. Figure of Merit versus Frequency

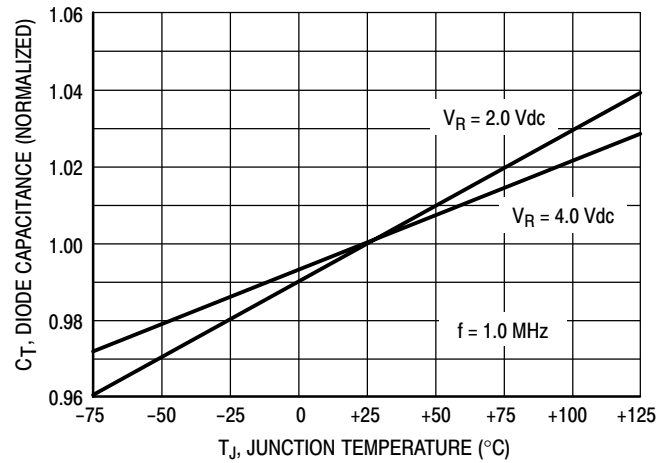


Figure 4. Diode Capacitance versus Temperature

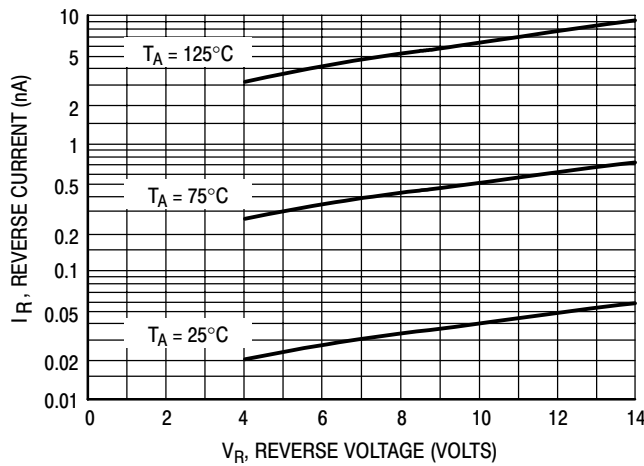


Figure 5. Reverse Current versus Reverse Voltage

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